

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

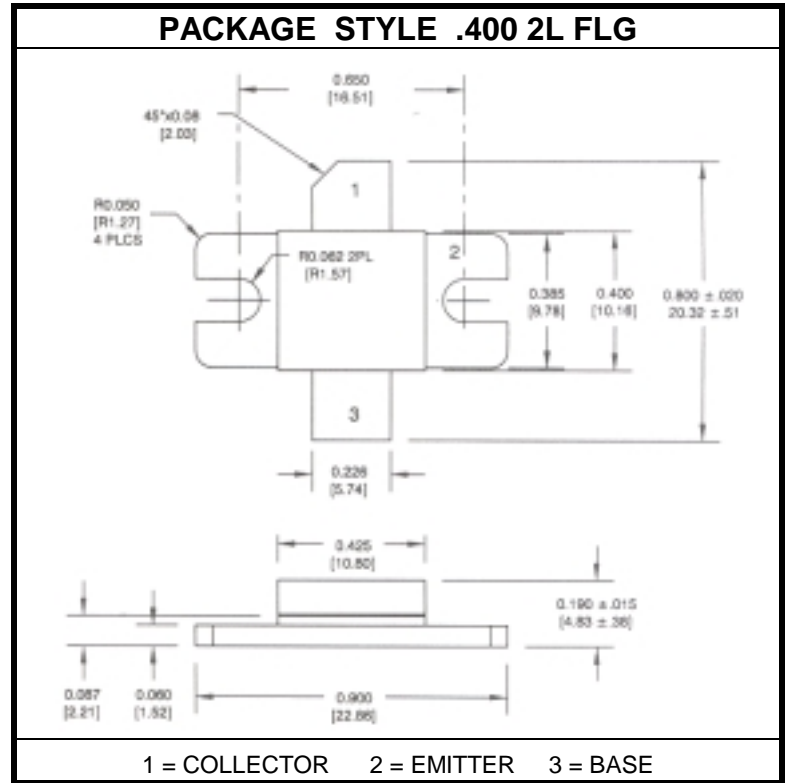
The **ASI PTB20111** is Designed for General Purpose Class AB Power Amplifier Applications up to 900 MHz.

FEATURES:

- 25 W, 860-900 MHz
- Silicon Nitride Passivated
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CB0}	65 V
P_{DISS}	159 W @ T _C = 25 °C
T_J	-40 °C to +150 °C
T_{STG}	-40 °C to +150 °C
θ_{JC}	1.1 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 100 mA			25			V
BV_{CES}	I _C = 100 mA			55			V
BV_{EBO}	I _E = 5.0 mA			3.5			V
h_{FE}	V _{CE} = 5.0 V	I _C = 1.0 A		20		100	---
P_G	V _{CC} = 25 V	P _{OUT} = 85 W	f = 900 MHz	8.5	9.5		dB
η_c	I _{CQ} = 200 mA			50			%
Ψ	V _{CC} = 25 V	P _{OUT} = 60 W	f = 900 MHz			10:1	---
	I _{CQ} = 200 mA						